**Abstract:**

**Process for producing $p^-$-doped and epitaxially coated semiconductor wafers from silicon**

The invention relates to a process for producing $p^-$ doped and epitaxially coated semiconductor wafers from silicon, wherein a silicon single crystal is pulled using the Czochralski method and during this pulling is doped with boron, hydrogen and nitrogen, and is processed to form $p^-$-doped semiconductor wafers which are epitaxially coated.

Fig. 13